

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	108495	(induct\$3 or deduct\$3 or causat\$3 or insulat\$3 or (low\$3 adj3 (dielectric or di-electric or dielectric)) near5 (constant or capacit\$3) same (less or low\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 20:59
L2	29211485	@ad<"20040722" or @rlad<"20040722"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:00
L3	2442	(first or second or third) near3 (fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:00
L4	31171	(fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (film or layer or dielectric or di-electric or dielectric) same (void or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:00
L5	579	L3 and L4	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/04 21:00
L6	447	L5 and L2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:01
L7	106	L1 and L6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:01
L8	2442	(first or second or third) near3 (fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:02
L9	31171	(fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (film or layer or dielectric or di-electric or dielectric) same (void or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:02

L10	579	L8 and L9	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/04 21:02
L11	106	L7 and L10	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:02
L12	14	((carbon near3 fluorocarbon) adj3 (film or gas or layer)) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:03
L13	0	L12 and L11	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:03
L14	34471	438/400-404,584-597,622- 624,637,672- 675,700,733,734,758-763,778- 780.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:04
L15	35	L14 and L11	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:04
L16	0	L15 and (((carbon near3 fluorocarbon) adj3 (film or gas or layer)) same (substrate or wafer or semiconductor))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:05
L17	0	L15 and ((carbon near3 fluorocarbon) adj3 (film or gas or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:05
S2	0	JP10-092804A	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 13:16
S3	0	JP 10-092804A	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 13:16

S4	0	"092804".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 13:17
S5	1	"6524963".PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/01 13:17
S6	1	"20070020951".PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/01 13:23
S7	2440	(first or second or third) near3 (fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 13:39
S8	31130	(fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (film or layer or dielectric or di-electric or di electric) same (void or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 13:41
S10	2440	(first or second or third) near3 (fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:13
S11	31130	(fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (film or layer or dielectric or di-electric or di electric) same (void or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:13
S12	579	S10 and S11	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/01 20:13
S13	0	(first or second or third) near3 ((carbon adj3 fluorocarbon) adj3 (film or gas or layer)) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:16
S14	2	(first or second or third) near3 (carbon adj3 fluorocarbon) adj3 (film or gas or layer) same (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:16
S15	29211053	@ad<"20040722" or @rlad<"20040722"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:18

S16	447	S12 and S15	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:19
S17	14	((carbon near3 fluorocarbon) adj3 (film or gas or layer)) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:21
S18	13	S17 and S15	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:21
S19	1	(first or second or third) near3 ((carbon adj3 fluorocarbon) adj3 (film or gas or layer)) near5 (void or hole or space)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:37
S20	2	("6531409" "6419985").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/02 11:54
S21	11596	(remov\$3 or cut\$3 or etch\$3) near3 (volatil\$3 or explosiv\$3 or unstabl\$3) same (carbon or fluorine or fluorocarbon or fluoride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 11:58
S22	902	(remov\$3 or cut\$3 or etch\$3) near3 (volatil\$3 or explosiv\$3 or unstabl\$3) same (carbon or fluorine or fluorocarbon or fluoride) with (void or vacuum or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 11:59
S23	29211485	@ad<"20040722" or @rlad<"20040722"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 11:59
S24	2442	(first or second or third) near3 (fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 12:01
S25	31171	(fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (film or layer or dielectric or di-electric or di electric) same (void or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 12:01

S26	579	S24 and S25	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/02 12:01
S27	2	S22 and S26	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/02 12:01
S28	6	("5900290" "6005291" "6071797" "6091081" "6215087").PN. OR ("6419985").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/02 12:02
S29	2	("5525447" "6121162").PN. OR ("6531409").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/02 12:03
S30	34	("6215087").URPN.	USPAT	ADJ	ON	2009/04/02 12:08
S31	149	((carbon adj3 fluoride) adj3 gas) or fluorocarbon adj3 film) same (induct\$3 or dielectric or di electric or di-electric)	USPAT	ADJ	ON	2009/04/02 12:15
S32	2	S22 and S31	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 12:15
S33	0	((carbon adj3 fluoride) adj3 gas) or fluorocarbon adj3 film) same (induct\$3 adj3 capacity)	USPAT	ADJ	ON	2009/04/02 12:18
S34	0	((carbon adj3 fluoride) adj3 gas) or fluorocarbon adj3 (film or layer)) same (induct\$3 adj3 capacity)	USPAT	ADJ	ON	2009/04/02 12:19
S35	34471	438/400-404,584-597,622- 624,637,672- 675,700,733,734,758-763,778- 780.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 12:30
S36	9	("20040006249" "20040161946" "20040175501" "20050176230" "20060040507" "20060264059" "6429518" "6524963" "6593246").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/02 12:41

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film and method for forming same).wsp